



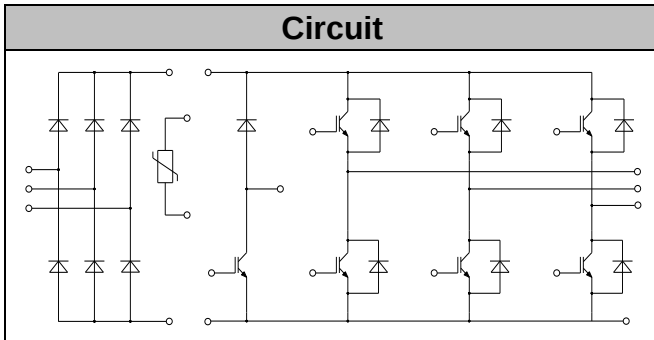
IGBT Modules

V_{CES}	1200V
I_C	150A

Applications

- Motor Drivers
- AC and DC servo drive amplifier
- UPS (Uninterruptible Power Supplies)

Circuit



Features

- Low switching losses
- Low $V_{CE(sat)}$ with positive temperature coefficient
- Including fast & soft recovery anti-parallel FWD
- Low inductance case
- High short circuit capability(8us)
- Maximum junction temperature 175°C

● IGBT- Inverter

Absolute Maximum Ratings

Parameter	Symbol	Conditions	Value	Unit
Collector-Emitter Voltage	V_{CES}	$V_{GE}=0V, I_C=1mA, T_{vj}=25^{\circ}C$	1200	V
Continuous Collector Current	I_C	$T_C=100^{\circ}C, T_{vjmax}=175^{\circ}C$	150	A
Repetitive Peak Collector Current	I_{CRM}	$t_p=1ms$	300	A
Gate-Emitter Voltage	V_{GES}	$T_{vj}=25^{\circ}C$	± 20	V
Total Power Dissipation	P_{tot}	$T_C=25^{\circ}C$ $T_{vjmax}=175^{\circ}C$	535	W



● IGBT- Inverter Characteristic Values

Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Gate-Emitter Threshold Voltage	$V_{GE(th)}$	$V_{GE}=V_{CE}, I_C=5mA, T_{vj}=25^{\circ}C$	5.0	6.0	6.6	V
Collector-Emitter Cut-off Current	I_{CES}	$V_{CE}=1200V, V_{GE}=0V, T_{vj}=25^{\circ}C$			1.0	mA
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=150A, V_{GE}=15V, T_{vj}=25^{\circ}C$		1.67		V
		$I_C=150A, V_{GE}=15V, T_{vj}=125^{\circ}C$		2.00		
		$I_C=150A, V_{GE}=15V, T_{vj}=150^{\circ}C$		2.1		
Gate Charge	Q_G			2.3		uC
Input Capacitance	C_{ies}	$V_{CE}=25V, V_{GE}=0V,$ $f=1MHz, T_{vj}=25^{\circ}C$		27.5		nF
Reverse Transfer Capacitance	C_{res}			0.1		nF
Gate-Emitter leakage current	I_{GES}	$V_{CE}=0V, V_{GE}=20V, T_{vj}=25^{\circ}C$			400	nA
Turn-on Delay Time	$t_{d(on)}$	$I_C=150A$ $V_{CE}=600V$ $V_{GE}=\pm 15V$ $R_G=3.3\Omega$ $T_{vj}=25^{\circ}C$		144		ns
Rise Time	t_r			80		ns
Turn-off Delay Time	$t_{d(off)}$			282		ns
Fall Time	t_f			182		ns
Energy Dissipation During Turn-on Time	E_{on}			14.3		mJ
Energy Dissipation During Turn-off Time	E_{off}			10.8		mJ
Turn-on Delay Time	$t_{d(on)}$	$I_C=150A$ $V_{CE}=600V$ $V_{GE}=\pm 15V$ $R_G=3.3\Omega$ $T_{vj}=150^{\circ}C$		162		ns
Rise Time	t_r			84		ns
Turn-off Delay Time	$t_{d(off)}$			357		ns
Fall Time	t_f			327		ns
Energy Dissipation During Turn-on Time	E_{on}			24.3		mJ
Energy Dissipation During Turn-off Time	E_{off}			6.9		mJ
SC Data	I_{sc}	$t_p \leq 8\mu s, V_{GE}=15V, T_{vj}=150^{\circ}C,$ $V_{CC}=600V, V_{CEM} \leq 1200V$		650		A



● Diode-Inverter

Absolute Maximum Ratings

Parameter	Symbol	Conditions	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	$T_{vj}=25^{\circ}\text{C}$	1200	V
Continuous DC Forward Current	I_F		150	A
Repetitive Peak Forward Current	I_{FRM}	$t_p=1\text{ms}$	300	A

Characteristic Values

Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Forward Voltage	V_F	$I_F=150\text{A}, T_{vj}=25^{\circ}\text{C}$		2.10	2.80	V
		$I_F=150\text{A}, T_{vj}=125^{\circ}\text{C}$		1.85		
		$I_F=150\text{A}, T_{vj}=150^{\circ}\text{C}$		1.78		
Recovered Charge	Q_{rr}	$I_F=150\text{A}$ $V_R=600\text{V}$ $-di_F/dt=1600\text{A/us}$ $T_{vj}=25^{\circ}\text{C}$		8.32		μC
Peak Reverse Recovery Current	I_{rr}			49		A
Reverse Recovery Energy	E_{rec}			3.1		mJ
Recovered Charge	Q_{rr}	$I_F=150\text{A}$ $V_R=600\text{V}$ $-di_F/dt=1600\text{A/us}$ $T_{vj}=150^{\circ}\text{C}$		30.15		μC
Peak Reverse Recovery Current	I_{rr}			92		A
Reverse Recovery Energy	E_{rec}			11.5		mJ



● IGBT-Brake-Chopper

Absolute Maximum Ratings

Parameter	Symbol	Conditions	Value	Unit
Collector-Emitter Voltage	V_{CES}	$V_{GE}=0V, I_C=1mA, T_{vj}=25^{\circ}C$	1200	V
Continuous Collector Current	I_C	$T_C=100^{\circ}C, T_{vjmax}=175^{\circ}C$	100	A
Repetitive Peak Collector Current	I_{CRM}	$t_p=1ms$	200	A
Gate-Emitter Voltage	V_{GES}	$T_{vj}=25^{\circ}C$	± 20	V
Total Power Dissipation	P_{tot}	$T_C=25^{\circ}C$ $T_{vjmax}=175^{\circ}C$	416	W

Characteristic Values

Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Gate-Emitter Threshold Voltage	$V_{GE(th)}$	$V_{GE}=V_{CE}, I_C=3mA, T_{vj}=25^{\circ}C$	5.0	6.0	6.5	V
Collector-Emitter Cut-off Current	I_{CES}	$V_{CE}=1200V, V_{GE}=0V, T_{vj}=25^{\circ}C$			1.0	mA
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=100A, V_{GE}=15V, T_{vj}=25^{\circ}C$		1.60		V
		$I_C=100A, V_{GE}=15V, T_{vj}=125^{\circ}C$		1.85		
		$I_C=100A, V_{GE}=15V, T_{vj}=150^{\circ}C$		1.95		
Gate Charge	Q_G			1.01		μC
Input Capacitance	C_{ies}	$V_{CE}=25V, V_{GE}=0V,$ $f=1MHz, T_{vj}=25^{\circ}C$		8.9		nF
Reverse Transfer Capacitance	C_{res}			0.21		nF
Gate-Emitter leakage current	I_{GES}	$V_{CE}=0V, V_{GE}=20V, T_{vj}=25^{\circ}C$			400	nA
Turn-on Delay Time	$t_{d(on)}$	$I_C=100A$ $V_{CE}=600V$ $V_{GE}=\pm 15V$ $R_G=3.9\Omega$ $T_{vj}=25^{\circ}C$		164		ns
Rise Time	t_r			44		ns
Turn-off Delay Time	$t_{d(off)}$			282		ns
Fall Time	t_f			179		ns
Energy Dissipation During Turn-on Time	E_{on}			7.09		mJ
Energy Dissipation During Turn-off Time	E_{off}			7.24		mJ



Turn-on Delay Time	$t_{d(on)}$	$I_C=100A$ $V_{CE}=600V$ $V_{GE}=\pm 15V$ $R_G=3.9\Omega$ $T_{vj}=150^\circ C$		174		ns
Rise Time	t_r			49		ns
Turn-off Delay Time	$t_{d(off)}$			352		ns
Fall Time	t_f			301		ns
Energy Dissipation During Turn-on Time	E_{on}			11.7		mJ
Energy Dissipation During Turn-off Time	E_{off}			10.5		mJ
SC Data	I_{sc}	$t_p \leq 8\mu s, V_{GE}=15V, T_{vj}=150^\circ C,$ $V_{CC}=600V, V_{CEM} \leq 1200V$		400		A

● Diode-Brake-Chopper

Absolute Maximum Ratings

Parameter	Symbol	Conditions	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	$T_{vj}=25^\circ C$	1200	V
Continuous DC Forward Current	I_F		60	A
Repetitive Peak Forward Current	I_{FRM}	$t_p=1ms$	120	A

Characteristic Values

Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Forward Voltage	V_F	$I_F=60A, T_{vj}=25^\circ C$		1.95	2.80	V
		$I_F=60A, T_{vj}=125^\circ C$		1.70		
		$I_F=60A, T_{vj}=150^\circ C$		1.65		
Recovered Charge	Q_{rr}	$I_F=60A$		5.6		μC
Peak Reverse Recovery Current	I_{rr}	$V_R=600V$ $-di_F/dt = 1500A/\mu s$		53		A
Reverse Recovery Energy	E_{rec}	$T_{vj}=25^\circ C$		1.83		mJ
Recovered Charge	Q_{rr}	$I_F=60A$		9.5		μC
Peak Reverse Recovery Current	I_{rr}	$V_R=600V$ $-di_F/dt = 1500A/\mu s$		57		A
Reverse Recovery Energy	E_{rec}	$T_{vj}=150^\circ C$		3.31		mJ



● Diode-Rectifier

Absolute Maximum Ratings

Parameter	Symbol	Conditions	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	$T_{vj}=25^{\circ}\text{C}$	1600	V
Average output Current 50/60Hz, sine wave	$I_{F(AV)}$	$T_C=100^{\circ}\text{C}$	150	A
Maximum RMS Current at Rectifier Output	I_{RMSM}	$T_C=100^{\circ}\text{C}$	150	A
Surge Forward Current	I_{FSM}	$V_R=0V, t_p=10\text{ms}, T_{vj}=25^{\circ}\text{C}$	1500	A
I^2t -value	I^2t	$V_R=0V, t_p=10\text{ms}, T_{vj}=25^{\circ}\text{C}$	11200	A^2s

Characteristic Values

Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Diode Forward Voltage	V_F	$I_F=150\text{A}, T_{vj}=150^{\circ}\text{C}$		1.2		V
Reverse Current	I_R	$T_{vj}=150^{\circ}\text{C}, V_R=1600\text{V}$			2.0	mA

● NTC-Thermistor

Characteristic Values

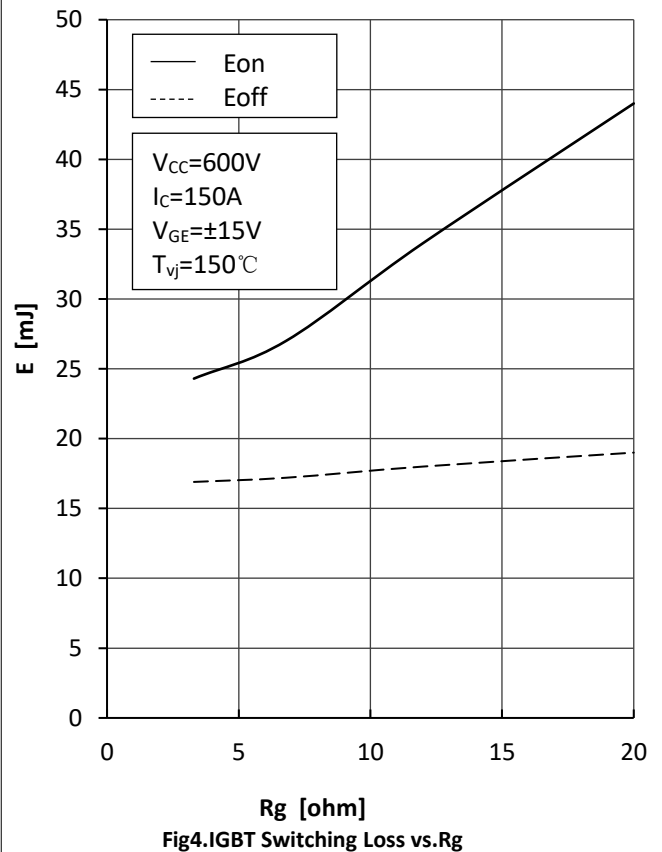
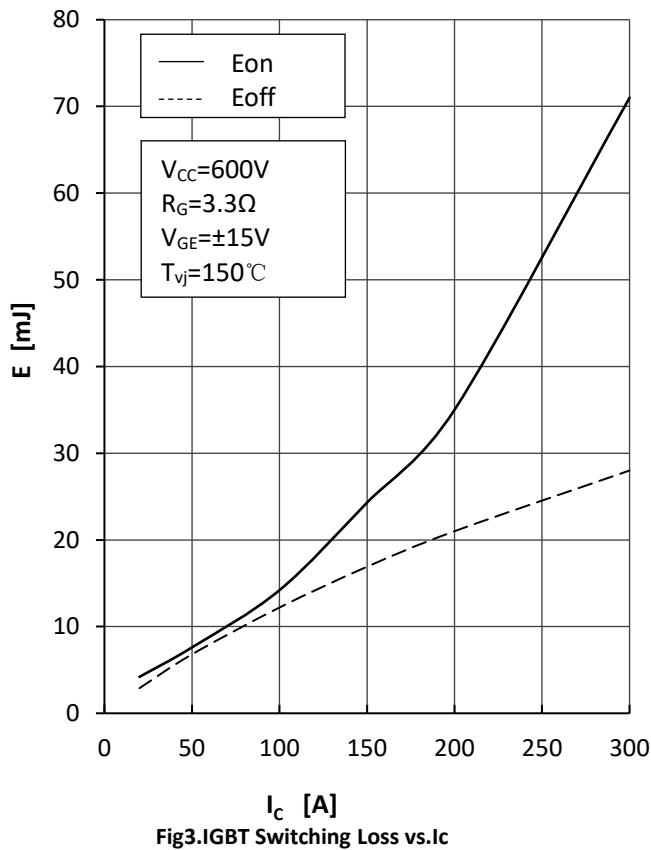
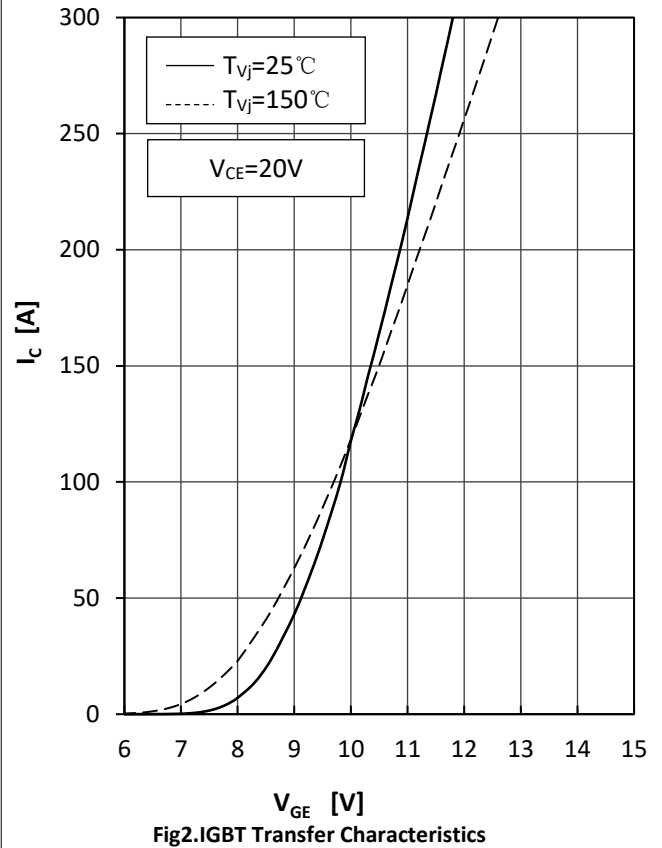
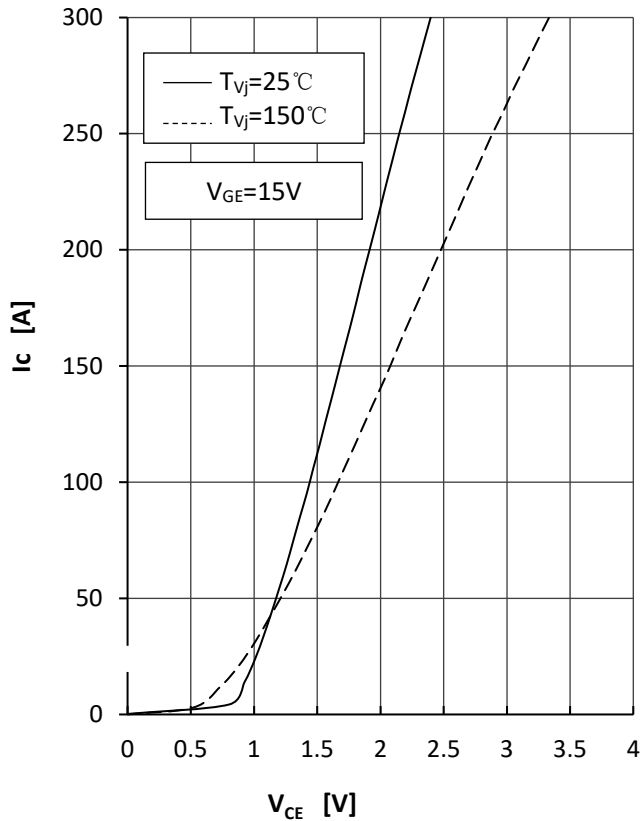
Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Rated Resistance	R_{25}			5.0		k Ω
Deviation of R100	$\Delta R/R$	$T_C=100, R_{100}=493.3\Omega$	-5		5	%
Power Dissipation	P_{25}				20.0	mW
B-value	$B_{25/50}$	$R_2=R_{25}\exp[B_{25/50}(1/T_2-1/(298.15\text{K}))]$		3375		K

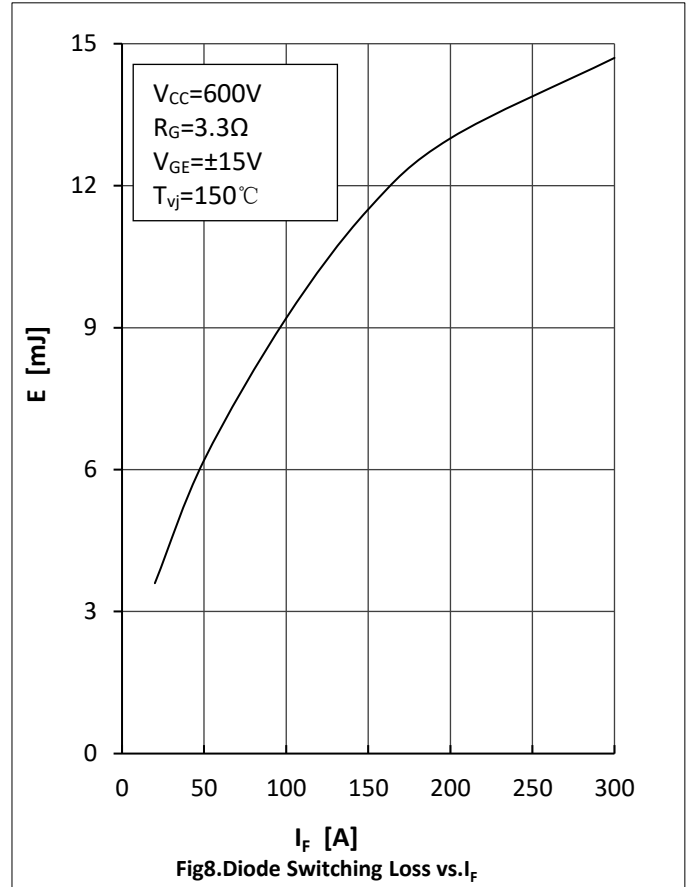
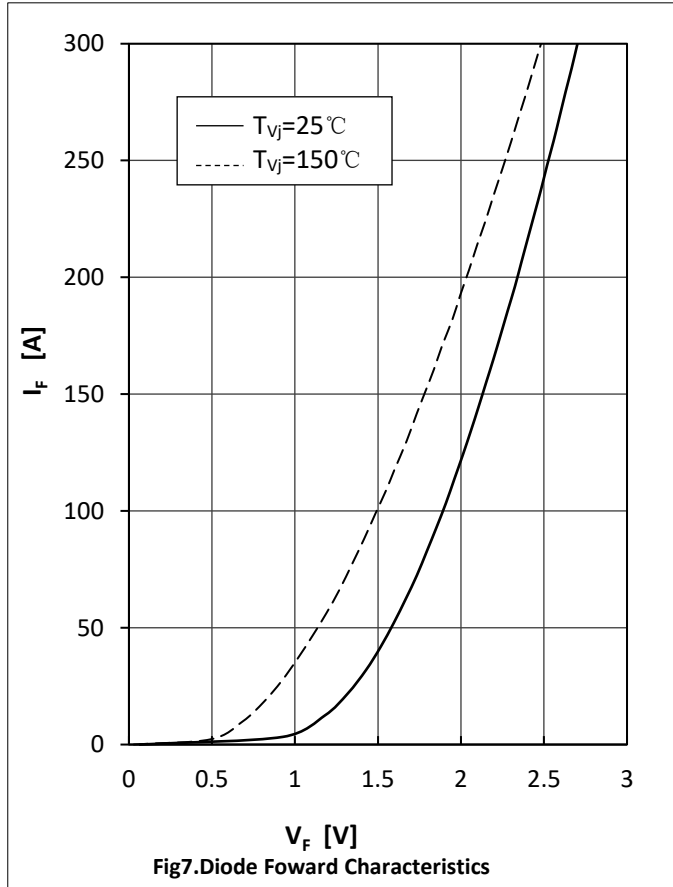
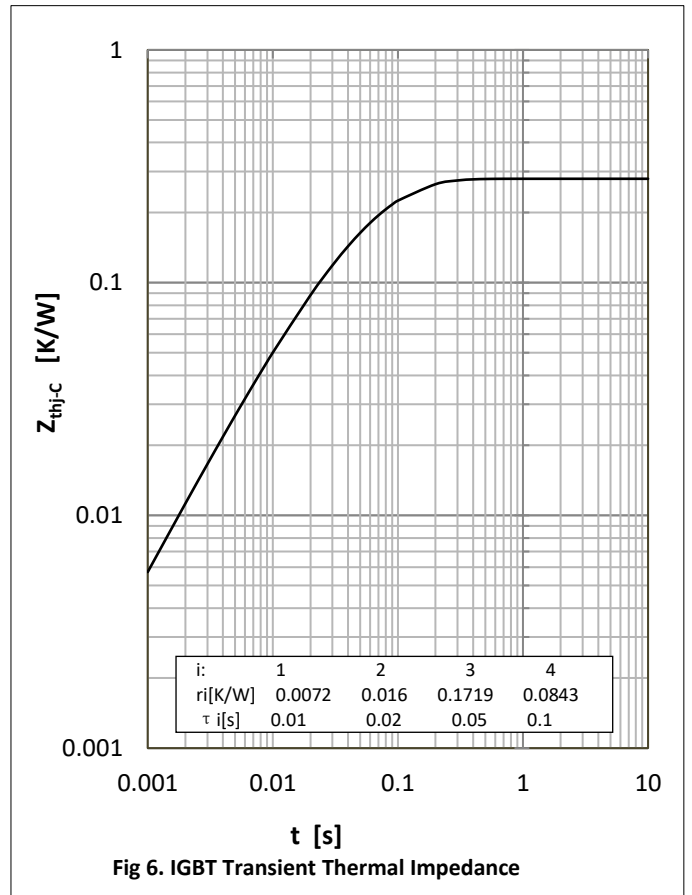
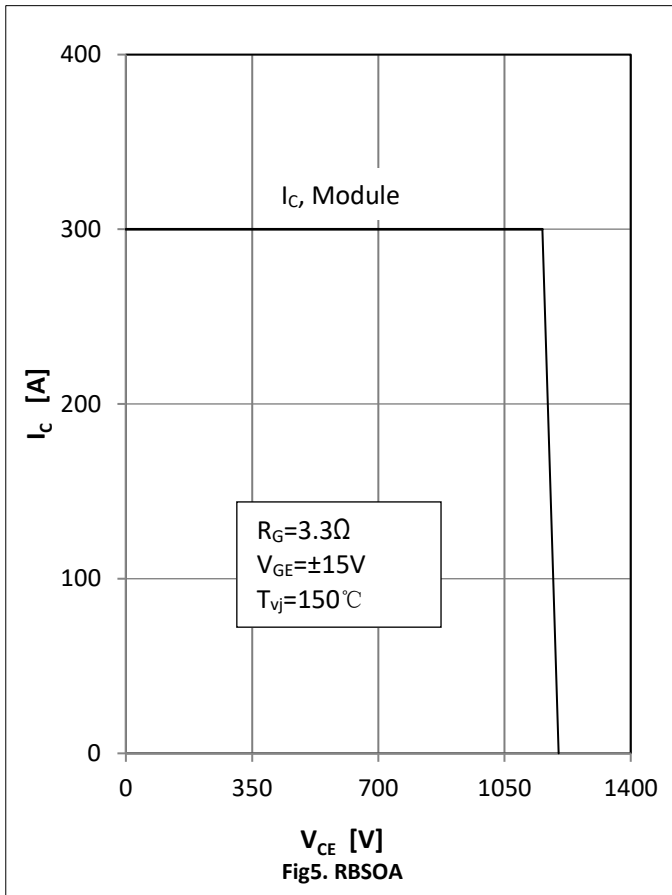


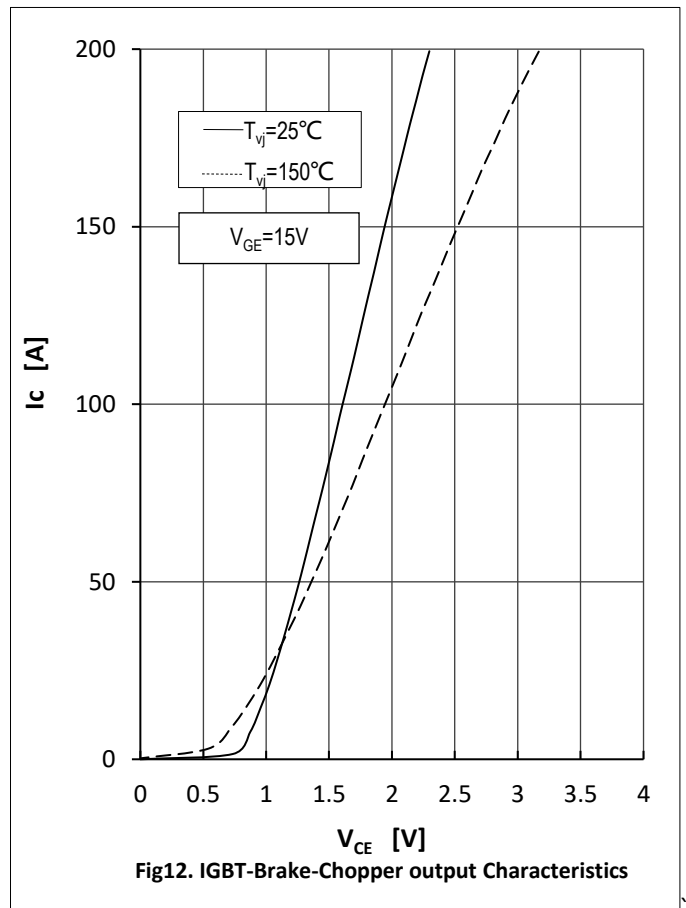
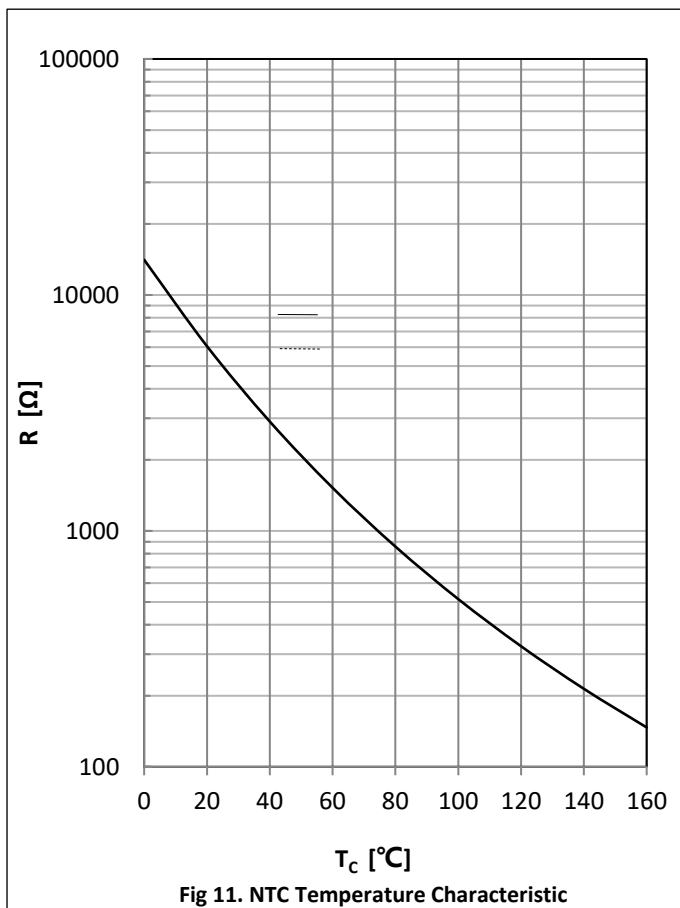
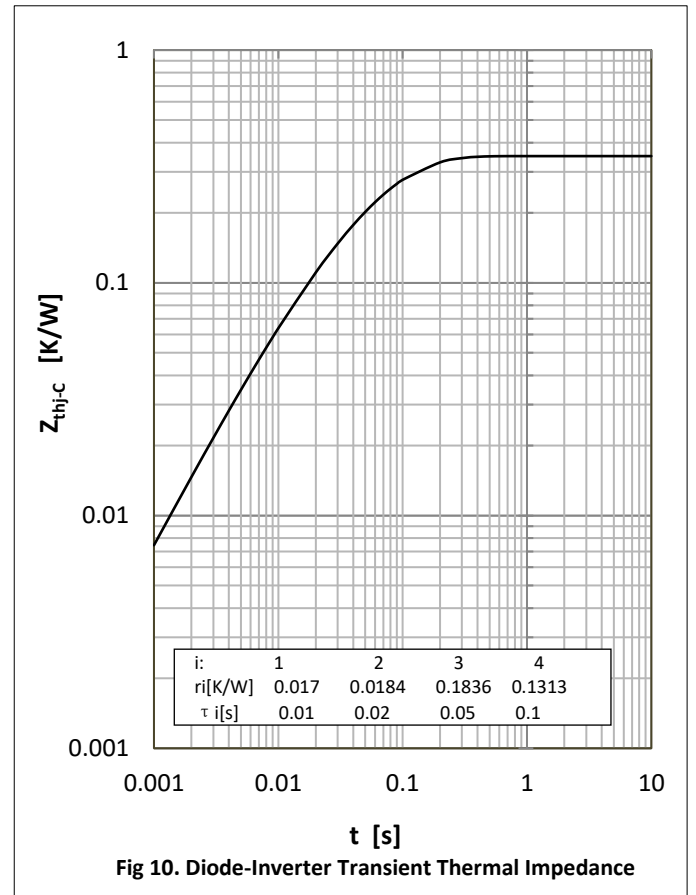
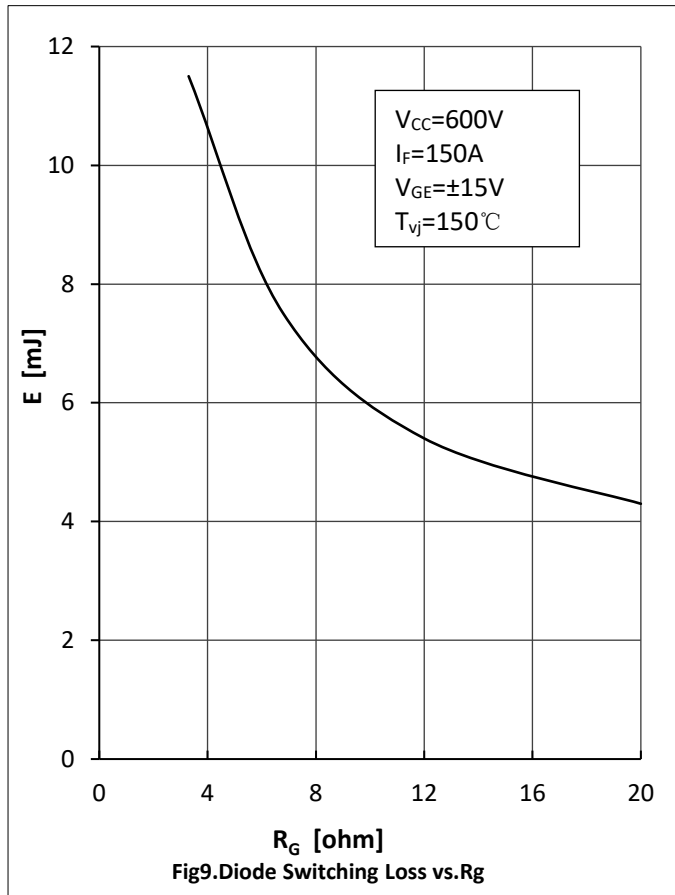
● Module Characteristics

$T_C=25^{\circ}\text{C}$ unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Isolation Voltage	V_{isol}	$t=1\text{min}, f=50\text{Hz}$	2500			V
Maximum Junction Temperature	$T_{j\text{max}}$				175	$^{\circ}\text{C}$
Operating Junction Temperature	$T_{vj\text{op}}$		-40		150	$^{\circ}\text{C}$
Storage Temperature	T_{stg}		-40		125	$^{\circ}\text{C}$
Stray-inductance-module	L_{SCE}			60		nH
Module Lead Resistance, Terminals-chip	$R_{\text{CC}'+\text{EE}'}$	$T_C=25^{\circ}\text{C}$, per switch		4.0		m Ω
	$R_{\text{AA}'+\text{CC}'}$			3.0		
Thermal Resistance Junction to Case	$R_{\theta\text{JC}}$	per IGBT-inverter			0.28	K/W
		per Diode-inverter			0.35	
		per IGBT-brake-copper			0.36	
		per Diode-brake-chopper			0.66	
		per Diode-rectifier			0.37	
Thermal Resistance Case to Sink	$R_{\theta\text{CS}}$	per Module		0.009		K/W
Module-to-Sink Torque	M_s		3.0		6.0	N·m
Weight of Module	G			300		g







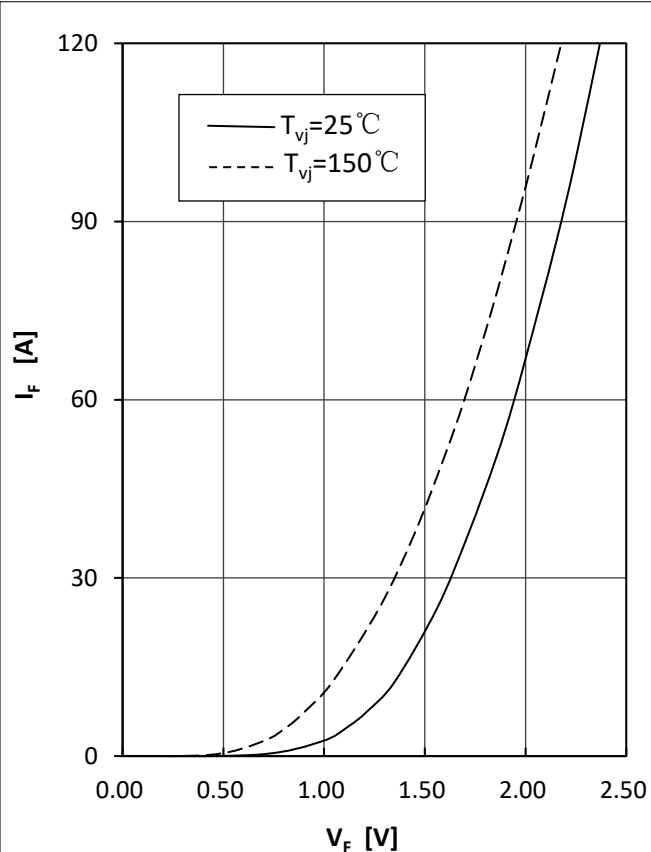


Fig13.Diode-Brake-Chopper Foward Characteristics

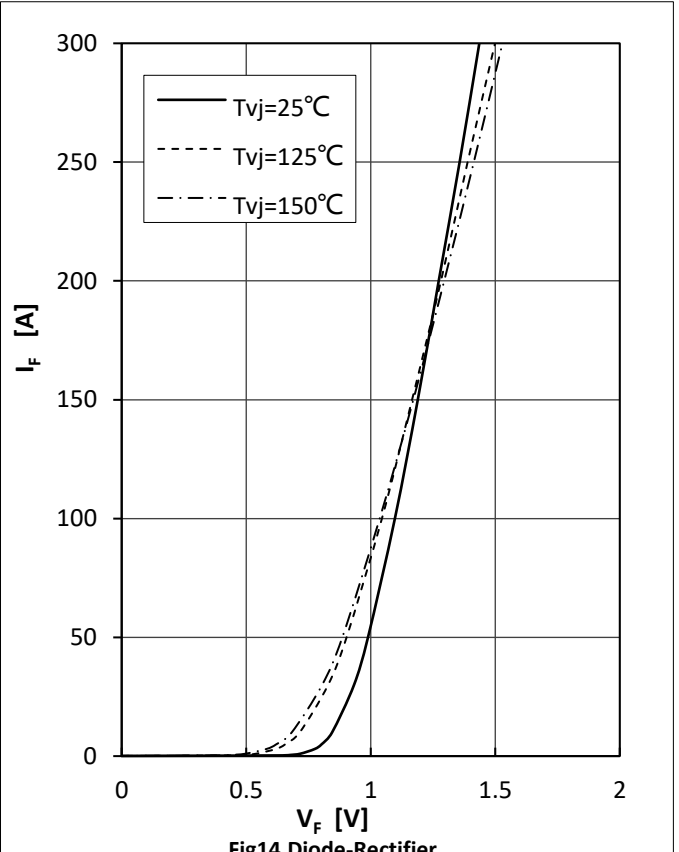
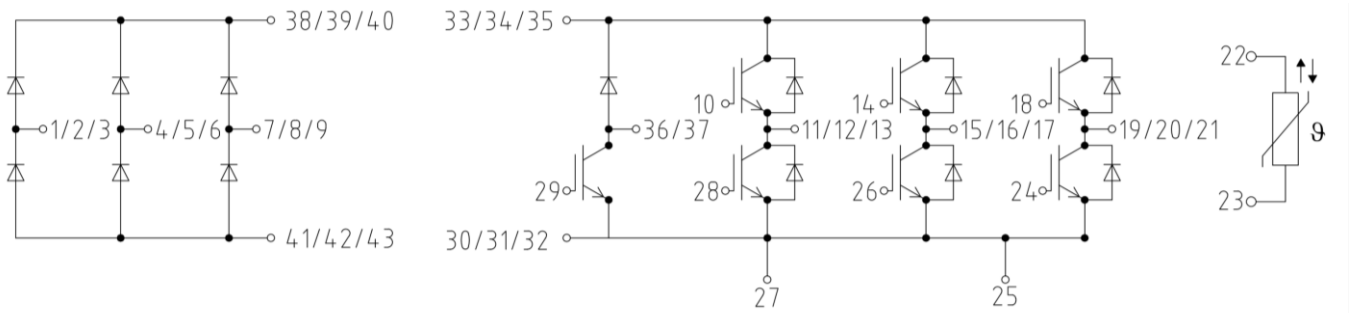


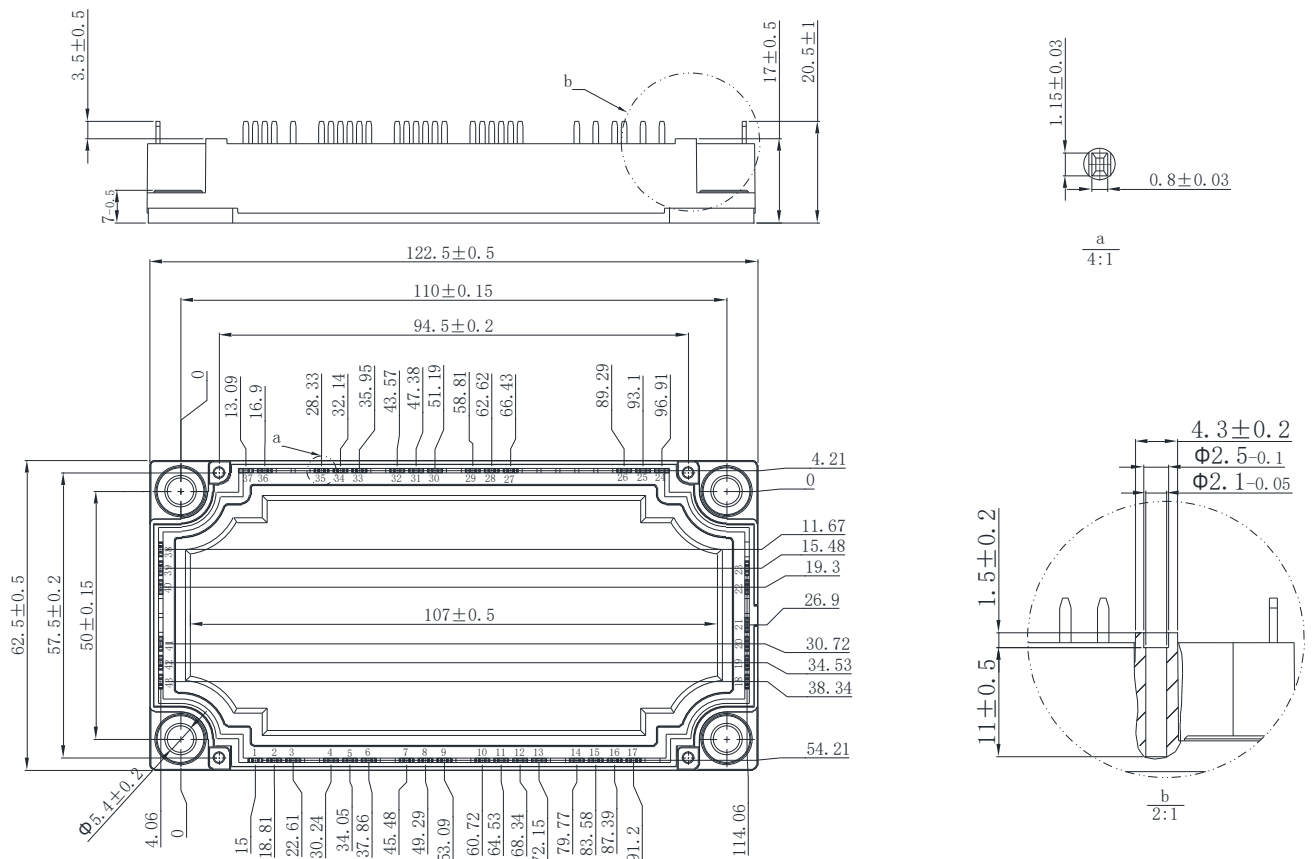
Fig14.Diode-Rectifier Foward Characteristics



● Circuit Diagram



● Package Outline Information





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